

cont
the first etching. Thus, according to the structure of the invention, high precision is ensured with respect to the shape of the thin film wiring.--

IN THE CLAIMS:

Please add new claim 17 as follows:

a² Supp
--17. (New) A semiconductor device according to claim 1, wherein the hard mask is resistant to heat at 400°C.--

REMARKS

At the time of the Office Action dated August 2, 2002, claims 1-16 were pending in this application. Of those claims, claims 1-5 have been rejected and claims 6-16 have been withdrawn from consideration pursuant to the provisions of 37 C.F.R. § 1.142(b).

Claim 17 has been added, and care has been exercised to avoid the introduction of new matter. Specifically, new claim 17 recites that the hard mask is resistant to heat at 400°C. Support for this limitation can be found on page 7, lines 8-19. Applicants submit that the present Amendment does not generate any new matter issue.

In the third enumerated paragraph of the statement of the rejection, the Examiner asserted that the title of the invention was not descriptive. In response, the Title has been changed to -- SEMICONDUCTOR DEVICE HAVING A LAYERED WIRING STRUCTURE WITH HARD MASK COVERING--.